# DTGN15N120 www.din-tek.jp

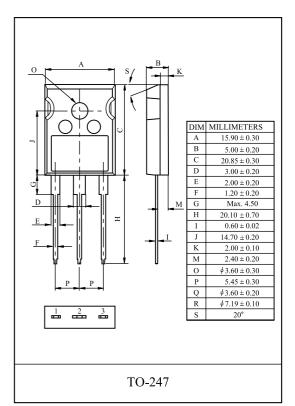
# **General Description**

Din-Tek Field Stop Trench IGBTs offer low switching losses, high energy efficiency and short circuit ruggedness.

It is designed for applications such as motor control, uninterrupted power supplies(UPS), general inverters.

#### FEATURES

- · High speed switching
- $\cdot$  High ruggedness, temperature stable behavior
- Short Circuit Withstand Times 10us
- · Extremely enhanced avalanche capability



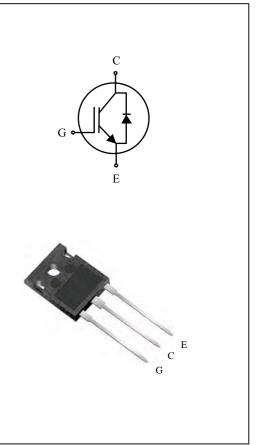
#### MAXIMUM RATING (Ta=25 )

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage	V <sub>GES</sub>	± 20	V	
Collector Current	@T <sub>C</sub> =25	- I <sub>C</sub>	30	А
	@T <sub>C</sub> =100	- <sup>1</sup> C	15	А
Pulsed Collector Current	I <sub>CM</sub> *	45	А	
Diode Continuous Forward Current @T <sub>C</sub> =100		I <sub>F</sub>	15	А
Diode Maximum Forward Current	I <sub>FM</sub>	45	А	
	@T <sub>C</sub> =25	- P <sub>D</sub>	167	W
Maximum Power Dissipation	@T <sub>C</sub> =100	I D	67	W
Maximum Junction Temperature		Tj	150	
Storage Temperature Range		T <sub>stg</sub>	-55 to + 150	

\*Repetitive rating : Pulse width limited by max. junction temperature

#### THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R <sub>thJC</sub>	0.75	/W
Thermal Resistance, Junction to Case (DIODE)	R <sub>thJC</sub>	2.0	/W
Thermal Resistance, Junction to Ambient	R <sub>thJA</sub>	40	/W



## **ELECTRICAL CHARACTERISTICS** (Ta=25)

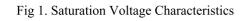
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static				1		
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	$V_{GE}=0V$ , $I_C=1.0mA$	1200	-	-	V
Collector Cut-off Current	I <sub>CES</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V	-	-	1.0	mA
Gate Leakage Current	I <sub>GES</sub>	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	±100	nA
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{GE} = V_{CE}$ , $I_C = 15 \text{mA}$	4.5	5.5	7.0	V
		V <sub>GE</sub> =15V, I <sub>C</sub> =15A	-	2.0	2.4	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$V_{GE}$ =15V, $I_C$ =15A, $T_C$ = 125	-	2.25	-	V
		V <sub>GE</sub> =15V, I <sub>C</sub> =30A	-	2.6	-	V
Dynamic				1		
Total Gate Charge	Qg		-	100	-	nC
Gate-Emitter Charge	Q <sub>ge</sub>	$V_{CC}$ =600V, $V_{GE}$ =15V, $I_{C}$ = 15A	-	15	-	nC
Gate-Collector Charge	Q <sub>gc</sub>		-	50	-	nC
Turn-On Delay Time	t <sub>d(on)</sub>	- $V_{CC}$ =600V, $I_{C}$ =15A, $V_{GE}$ =15V, $R_{G}$ =10 - Inductive Load, $T_{C}$ = 25	-	30	-	ns
Rise Time	t <sub>r</sub>		-	20	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	120	-	ns
Fall Time	t <sub>f</sub>		-	110	-	ns
Turn-On Switching Loss	Eon		-	1.0	1.3	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	0.55	0.75	mJ
Total Switching Loss	E <sub>ts</sub>		-	1.55	2.05	mJ
Turn-On Delay Time	t <sub>d(on)</sub>		-	30	-	ns
Rise Time	t <sub>r</sub>		-	20	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	130	-	ns
Fall Time	t <sub>f</sub>	$V_{CC}$ =600V, $I_C$ =15A, $V_{GE}$ =15V, $R_G$ =10 Inductive Load, $T_C$ = 125	-	220	-	ns
Turn-On Switching Loss	Eon		-	1.15	-	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	1.0	-	mJ
Total Switching Loss	E <sub>ts</sub>		-	2.15	-	mJ
Input Capacitance	C <sub>ies</sub>		-	1600	2080	pF
Ouput Capacitance	C <sub>oes</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz	-	75	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>		-	45	-	pF
Short Circuit Withstand Time	t <sub>sc</sub>	V <sub>CC</sub> =600V, V <sub>GE</sub> =15V, T <sub>C</sub> =100	10	-	-	μs

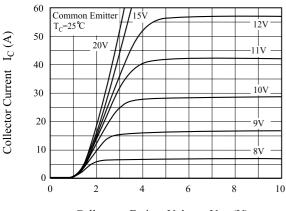
# ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V <sub>F</sub>	$I_F = 15A$	T <sub>C</sub> =25	-	2.4	3.0	- V
			T <sub>C</sub> =125	-	2.5	-	
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15A di/dt = 200A/ <b>µs</b>	T <sub>C</sub> =25	-	115	-	ns
			T <sub>C</sub> =125	-	140	-	
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		T <sub>C</sub> =25	-	12.5	-	А
			T <sub>C</sub> =125	-	14.0	-	А
Diode Reverse Recovery Charge	Q <sub>rr</sub>		T <sub>C</sub> =25	-	0.75	-	μC
			T <sub>C</sub> =125	-	1.15	-	



# **Typical Performance Characteristics**





Collector - Emitter Voltage  $V_{CE}(V)$ 

Fig 3. Saturation Voltage vs. Case Temperature

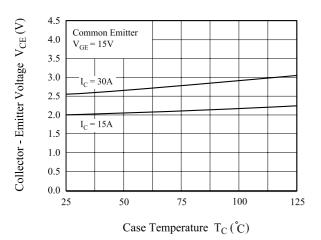
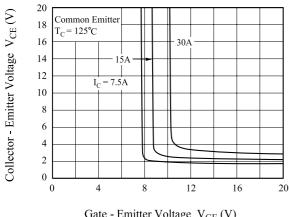
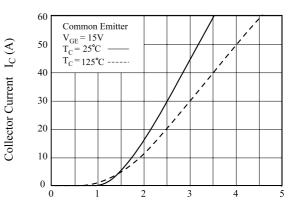


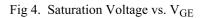
Fig 5. Saturation Voltage vs. VGE



Gate - Emitter Voltage V<sub>GE</sub> (V)



Collector - Emitter Voltage V<sub>CE</sub> (V)



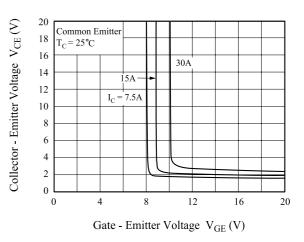
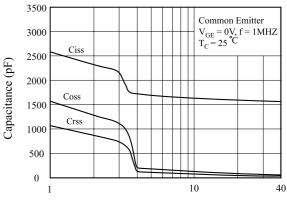


Fig 6. Capacitance Characteristics



Collector - Emitter Voltage  $V_{CE}(V)$ 

Fig 2. Saturation Voltage Characteristics



## Typical Performance Characteristics (Continued)

Fig 7. Turn-On Characteristics vs. Gate Resistance

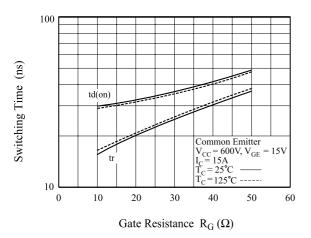


Fig 9. Switching Loss vs. Gate Resistance

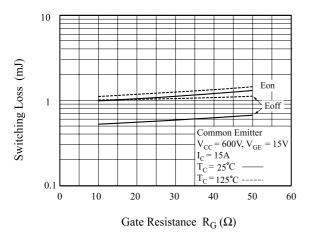
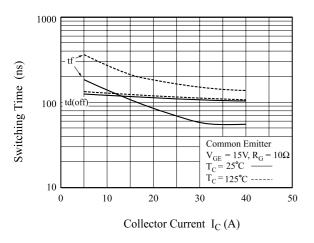


Fig 11. Turn-Off Characteristics vs. Collector Current



1000 td(off) Switching Time (ns) 100 Common Emitter  $V_{CC} = 600V, V_{GE} = 15V$  $I_C = 15A$  $\tilde{T_C} = 25^{\circ}C$  $T_{C} = 125^{\circ}C$  -----10 10 0 20 30 40 50 60 Gate Resistance  $R_{G}(\Omega)$ 



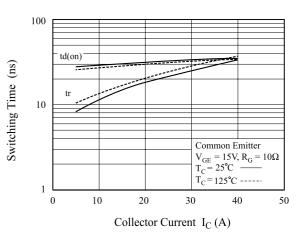


Fig 12. Switching Loss vs. Collector Current

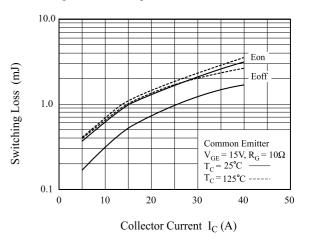
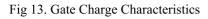
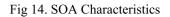


Fig 8. Turn-Off Characteristics vs. Gate Resistance

## **Typical Performance Characteristics (Continued)**





DC

100

1000

ΗI

10

Collector-Emitter Voltage  $V_{CE}(V)$ 

100.00

10.00

1.00

0.10

0.01

0.1

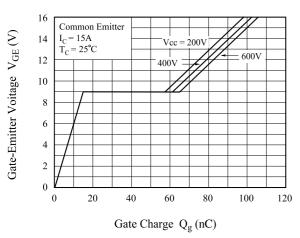
Collector Current I<sub>C</sub> (A)

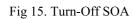
++++++ Single nonrepetitive pulse

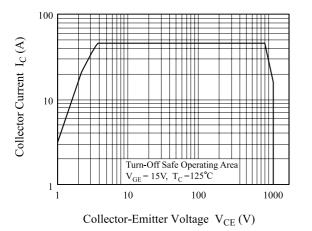
 $T_c = 25^{\circ}C$ Curves must be derated

linearly with increase in temperature

1







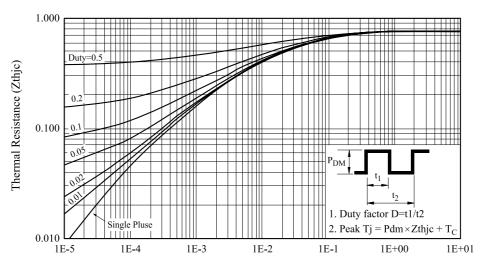
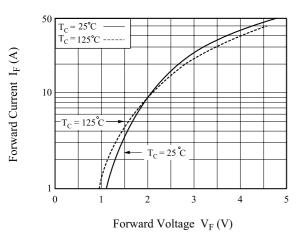


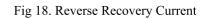
Fig 16. Transient Thermal Impedance of IGBT



### **Typical Performance Characteristics**







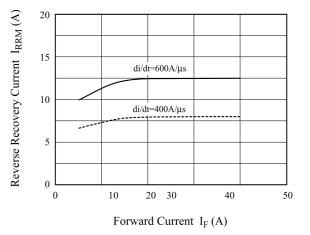
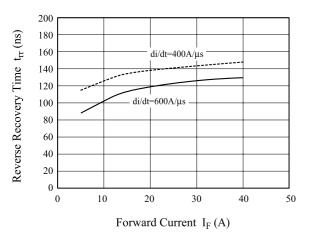


Fig 19. Reverse Recovery Time





### **Definition Switching Time & Loss.**

Fig 20. Switching Test Circuit

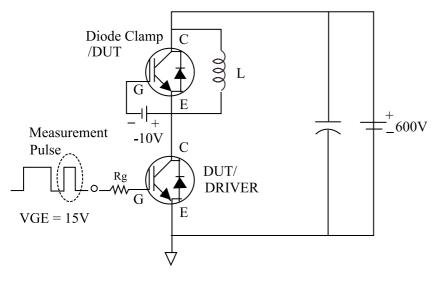


Fig 21. Definition Switching Time & Loss

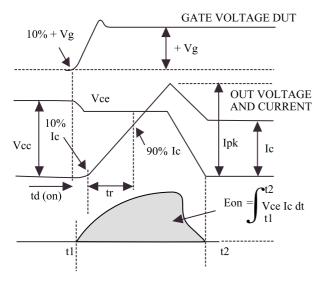
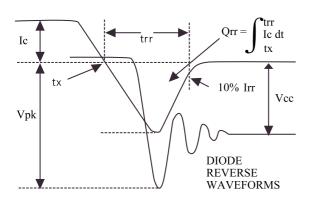
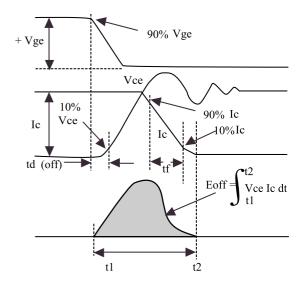


Fig 22. Definition Diode Switching Time







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